

Product data sheet

## 1. General description

Dual ultrafast power diode in a SOT78 (TO-220AB) plastic package.

## 2. Features and benefits

- Very low forward voltage drop
- Fast switching
- Soft recovery characteristic
- High reverse surge capability
- High thermal cycling performance
- Low thermal resistance

## 3. Applications

• Output rectifiers in high-frequency switched-mode power supplies

## 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	-	200	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 114 °C; SQW; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	15	A
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 114 °C; SQW; both diodes conducting	-	-	30	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode; <u>Fig. 4</u>	-	-	150	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode; Fig. 4	-	-	165	A
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 k $\Omega$	-	-	8	kV
Static char	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	0.95	1.05	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1	1.2	V
		I <sub>F</sub> = 15 A; T <sub>i</sub> = 150 °C; <u>Fig. 6</u>	-	0.78	0.85	V





#### Dual ultrafast power diode

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Dynamic chara	acteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery; Fig. 7}$	-	18	25	ns

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	К	cathode		
3	A2	anode 2		r sym125
mb	К	mounting base; cathode	TO-220AB (SOT78)	

# 6. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BYQ42E-200	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

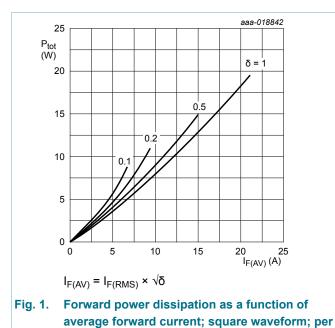
Dual ultrafast power diode

## 7. Limiting values

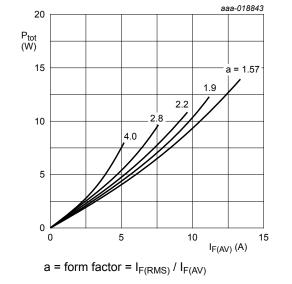
#### Table 4.Limiting values

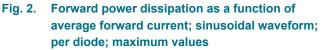
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	200	V
V <sub>RWM</sub>	crest working reverse voltage		-	200	V
V <sub>R</sub>	reverse voltage	DC	-	200	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 114 °C; SQW; <u>Fig. 1</u> ; Fig. 2; Fig. 3	-	15	A
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 114 °C; SQW; both diodes conducting	-	30	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode; <u>Fig. 4</u>	-	150	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode; Fig. 4	-	165	A
I <sub>RRM</sub>	repetitive peak reverse current	δ = 0.0010; t <sub>p</sub> = 2 μs	-	0.2	А
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs	-	0.2	A
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 k $\Omega$	-	8	kV



diode; maximum values

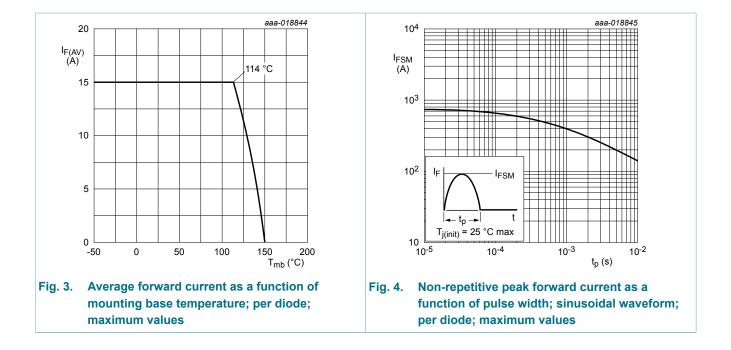




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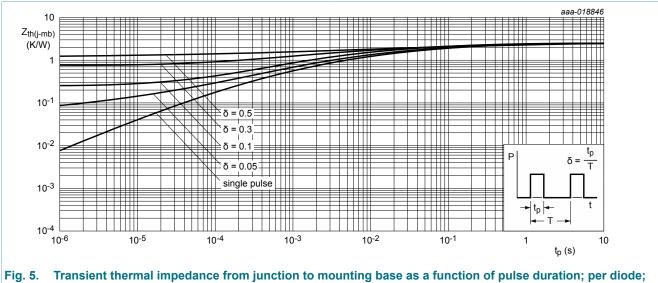
#### Dual ultrafast power diode



Dual ultrafast power diode

## 8. Thermal characteristics

Table 5. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5	-	-	2.4	K/W
	mounting base	with heatsink compound; both diodes conducting	-	-	1.4	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air		-	60	-	K/W

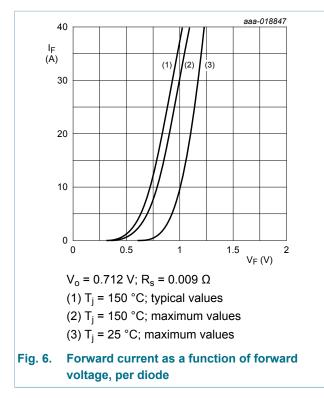


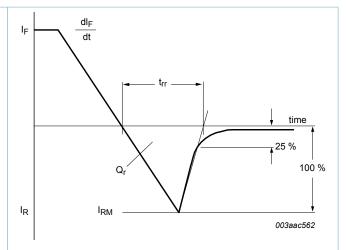
#### maximum values

Dual ultrafast power diode

## 9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · · ·				
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	0.95	1.05	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1	1.2	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	0.78	0.85	V
I <sub>R</sub> reverse current		V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C	-	3	20	μA
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 150 °C	-	0.3	1	mA
Dynamic cł	naracteristics	· · · · ·	I			
Q <sub>r</sub> recovered charge	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	6	15	nC
		$I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/µs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	10	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/µs; T <sub>j</sub> = 25 °C; ramp recovery; Fig. 7	-	18	25	ns
RM	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}_F/\text{d}t = 100 \text{ A}/\mu\text{s};$ $T_i = 25 \text{ °C}; \text{ Fig. 7}$	-	1	-	A

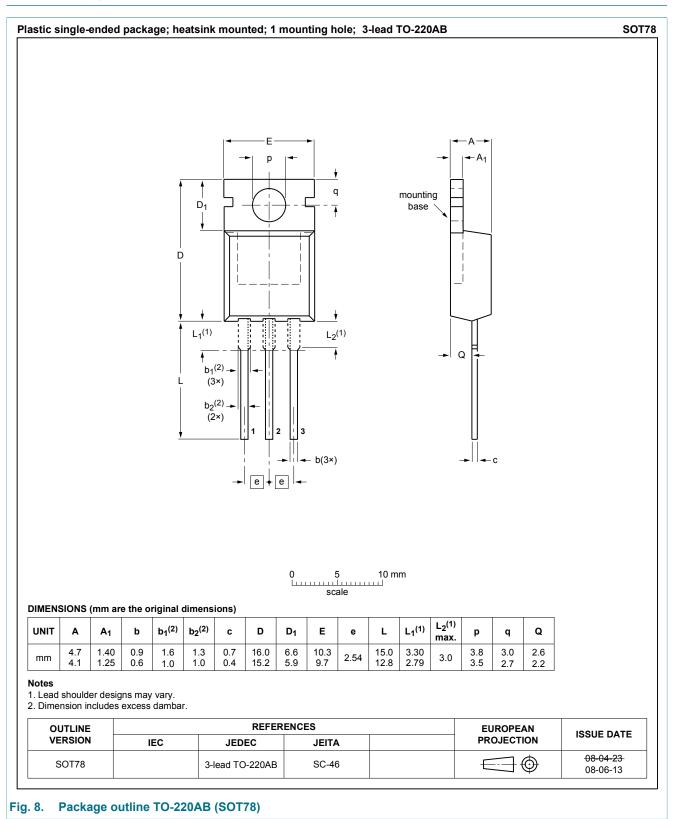






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## 10. Package outline



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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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